

isc Silicon PNP Darlington Power Transistor
BDV64/A/B/C
DESCRIPTION

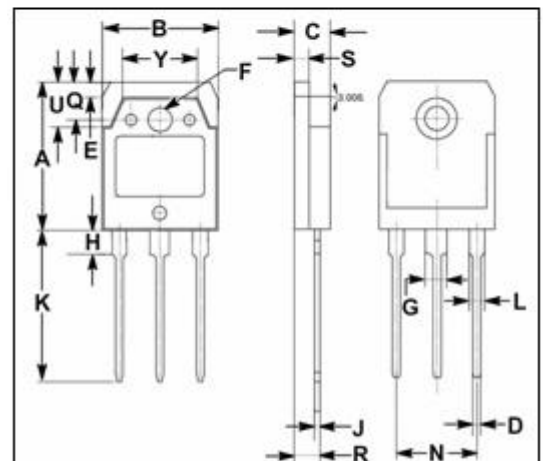
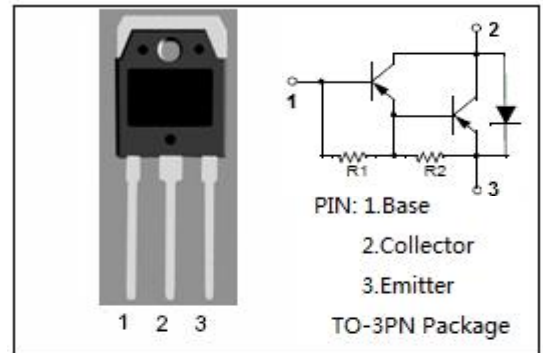
- Collector Current $-I_C = -12A$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = -2.0V(\text{Max.}) @ I_C = -5A$
- Complement to Type BDV65/A/B/C
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for audio output stages and general amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT	
V_{CBO}	Collector-Base Voltage	BDV64	-60	V
		BDV64A	-80	
		BDV64B	-100	
		BDV64C	-120	
V_{CEO}	Collector-Emitter Voltage	BDV64	-60	V
		BDV64A	-80	
		BDV64B	-100	
		BDV64C	-120	
V_{EBO}	Emitter-Base Voltage	-5	V	
I_C	Collector Current-Continuous	-12	A	
I_{CM}	Collector Current-Peak	-20	A	
I_B	Base Current-Continuous	-0.5	A	
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	125	W	
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	3.5		
T_J	Junction Temperature	150	$^\circ\text{C}$	
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$	




DIM	mm	
	MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.0	$^{\circ}C/W$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	35.7	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS
 $T_C=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	BDV64 	-60			V	
		BDV64A	-80				
		BDV64B	-100				
		BDV64C	-120				
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -5A; I_B = -20mA$			-2.0	V	
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -5A; V_{CE} = -4V$			-2.5	V	
I_{CEO}	Collector Cutoff Current	$V_{CE} = \frac{1}{2}V_{CE0max}; I_B = 0$			-2.0	mA	
I_{CBO}	Collector Cutoff Current	BDV64	$V_{CB} = -40V; I_E = 0; T_J = 150^{\circ}C$			-2.0	mA
		BDV64A	$V_{CB} = -50V; I_E = 0; T_J = 150^{\circ}C$				
		BDV64B	$V_{CB} = -60V; I_E = 0; T_J = 150^{\circ}C$				
		BDV64C	$V_{CB} = -70V; I_E = 0; T_J = 150^{\circ}C$				
I_{CBO}	Collector Cutoff Current	$V_{CB} = V_{CB0max}; I_E = 0$			-0.4	mA	
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5V; I_C = 0$			-5	mA	
h_{FE}	DC Current Gain	$I_C = -5A; V_{CE} = -4V$	1000				

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